| | Hits | Search Text | DBs |
|----|------|---|----------|
| 23 | 1 | (((cell or memory or array or Rmemo) near9 (trench\$3 or STI)) same (larger or deeper or steeper or deep or steep) same (pad near9 nitride) same etch\$4 same ((Rperiph\$6 or periph\$5) near9 (trench\$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same (shallow\$4 or narrow\$4) same etch\$4 same (pad near9 nitride) same ((dop\$4 or (ion near5 implant\$5) or implant\$4) near9 substrate near9 surface)) | US-PGPUB |
| 24 | 1 | (((cell or memory or array or Rmemo) near9 (trench\$3 or STI)) same (larger or deeper or steeper or deep or steep) same (pad near9 nitride) same etch\$4 same ((Rperiph\$6 or periph\$5) near9 (trench\$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same (shallow\$4 or narrow\$4) same etch\$4 same ((dop\$4 or (ion near5 implant\$5) or implant\$4) near9 substrate near9 surface)) | |

| | Hits | Search Text | DBs |
|----|------|---|---|
| 25 | 1 | ((Rperiph\$6 or periph\$5) heary (trench\$3 or STI))) and gate and source and drain and ((memory or array or cell or Rmemo) same | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB |